

Hongfei Li

List of Publications by Year in descending order

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Version: 2024-02-01

18
papers

364
citations

759055

12
h-index

839398

18
g-index

18
all docs

18
docs citations

18
times ranked

706
citing authors

#	ARTICLE	IF	CITATIONS
1	Extending the metal-induced gap state model of Schottky barriers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, .	0.6	14
2	Modeling of surface gap state passivation and Fermi level de-pinning in solar cells. Applied Physics Letters, 2019, 114, .	1.5	20
3	Dye-Assisted Transformation of Cu ₂ O Nanocrystals to Amorphous Cu _x O Nanoflakes for Enhanced Photocatalytic Performance. ACS Omega, 2018, 3, 1939-1945.	1.6	13
4	Oxygen vacancies and hydrogen in amorphous In-Ga-Zn-O and ZnO. Physical Review Materials, 2018, 2, .	0.9	21
5	Controlling Surface Termination and Facet Orientation in Cu ₂ O Nanoparticles for High Photocatalytic Activity: A Combined Experimental and Density Functional Theory Study. ACS Applied Materials & Interfaces, 2017, 9, 8100-8106.	4.0	99
6	Yttrium passivation of defects in GeO ₂ and GeO ₂ /Ge interfaces. Applied Physics Letters, 2017, 110, .	1.5	12
7	The role of nitrogen doping in ALD Ta ₂ O ₅ and its influence on multilevel cell switching in RRAM. Applied Physics Letters, 2017, 110, .	1.5	54
8	Enhanced switching stability in Ta ₂ O ₅ resistive RAM by fluorine doping. Applied Physics Letters, 2017, 111, .	1.5	21
9	Germanium oxidation occurs by diffusion of oxygen network interstitials. Applied Physics Letters, 2017, 110, 222902.	1.5	9
10	Hydrogen and the Light-Induced Bias Instability Mechanism in Amorphous Oxide Semiconductors. Scientific Reports, 2017, 7, 16858.	1.6	19
11	Defect Emission and Optical Gain in SiC _x O _y :H Films. ACS Applied Materials & Interfaces, 2017, 9, 22725-22731.	4.0	13
12	Face Dependence of Schottky Barriers Heights of Silicides and Germanides on Si and Ge. Scientific Reports, 2017, 7, 16669.	1.6	14
13	Ab-initio simulations of higher Miller index Si:SiO ₂ interfaces for fin field effect transistor and nanowire transistors. Journal of Applied Physics, 2016, 119, .	1.1	6
14	AlN and Al oxy-nitride gate dielectrics for reliable gate stacks on Ge and InGaAs channels. Journal of Applied Physics, 2016, 119, .	1.1	7
15	Effect of metal oxide additions to quality on Ge/GeO ₂ interfaces. Journal of Applied Physics, 2016, 120, .	1.1	2
16	Dopant compensation in HfO ₂ and other high K oxides. Applied Physics Letters, 2014, 104, 192904.	1.5	13
17	Defects at Ge:GeO ₂ and Ge:MeOx interfaces. Microelectronic Engineering, 2013, 109, 244-249.	1.1	7
18	Identifying a suitable passivation route for Ge interfaces. Applied Physics Letters, 2012, 101, 052903.	1.5	20